

Please replace the paragraph beginning on page 14, line 9, with the following rewritten paragraph.

-- The dual read particularly addresses a wide number of potential problems in ferroelectric memories with a polymer memory material. First, the comparison can be established with a margin close to zero. Consequently, in a fatigued memory cell where the charge is released at a lower level and occurs slower, the sensing device will still distinguish the state since the total charge released in a first time period is greater than that released in a subsequent (equivalent) time period. There is no need for a-priori knowledge of the level of fatigue to properly sense the memory cell value. Similarly, following imprint, the absolute magnitude of the charge released in any given first time period is reduced due to the shift in the coercive field, but the relative value is still ordered. Again, the state of the memory cell can be determined with the dual slope integration without knowledge of the imprint magnitude. --

IN THE CLAIMS:

Please cancel claims 2 without prejudice or disclaimer.

Please amend claims 1 and 3 as follows:

1. (Twice Amended) A sensing device for reading data stored in a passive matrix memory comprising memory cells in the form of ferroelectric capacitors, wherein said sensing device